

# 2SB1435

## Silicon PNP Epitaxial Planar Type

### AF Output Amplifier

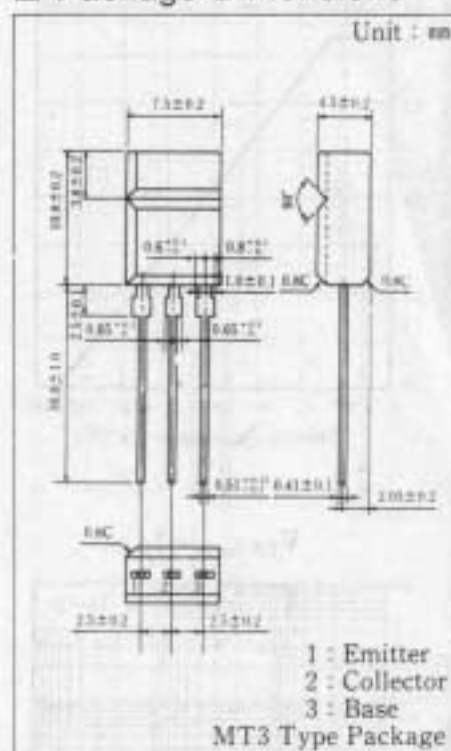
#### ■ Features

- Low collector-emitter saturation voltage ( $V_{CE(sat)}$ )
- High collector current ( $I_C$ )
- Automatic mounting by radial taping is possible.

#### ■ Absolute Maximum Ratings ( $T_a=25^\circ\text{C}$ )

Item	Symbol	Value	Unit
Collector-base voltage	$V_{CBO}$	-50	V
Collector-emitter voltage	$V_{CEO}$	-50	V
Emitter-base voltage	$V_{EBO}$	-5	V
Peak collector current	$I_{CP}$	-3	A
Collector current	$I_C$	-2	A
Collector power dissipation	$P_C$	1.5	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 ~ +150	$^\circ\text{C}$

#### ■ Package Dimensions



#### ■ Electrical Characteristics ( $T_c=25^\circ\text{C}$ )

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = -20\text{V}, I_E = 0$			-0.1	$\mu\text{A}$
Collector-base voltage	$V_{CEO}$	$I_C = -10\mu\text{A}, I_E = 0$	-50			V
Collector-emitter voltage	$V_{CEO}$	$I_C = -1\text{mA}, I_B = 0$	-50			V
Emitter cutoff current	$V_{EBO}$	$I_E = -10\mu\text{A}, I_C = 0$	-5			V
DC current gain	$h_{FE1}$	$V_{CB} = -2\text{V}, I_C = -200\text{mA}$	120		340	
	$h_{FE2}$	$V_{CE} = -2\text{V}, I_C = -1\text{A}$	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1\text{A}, I_B = -50\text{mA}$		-0.2	-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1\text{A}, I_B = -50\text{mA}$		-0.85	-1.2	V
Transition frequency	$f_T$	$V_{CB} = -10\text{V}, I_E = 50\text{mA}, f = 200\text{MHz}$		80		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		45	60	pF